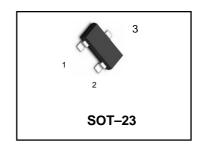


FEATURES

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

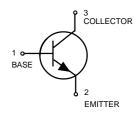
MAXIMUM RATINGS

Rating	Symbol	V al	ue LMBTA06	Unit
Collector–Emitter Voltage	V _{CEO}	60	80	Vdc
Collector-Base Voltage	V _{CBO}	60	80	Vdc
Emitter-Base Voltage	V _{EBO}	4.	.0	Vdc
Collector Current — Continuous	Ιc	50	00	mAdc



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR- 5 Board, (1)	P _D	225	mW
T _A = 25°C Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate, (2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T_J,T_stg	-55 to +150	°C



DEVICE MARKING

(S-)LMBTA05LT1G = 1H, (S-)LMBTA06LT1G = 1GM;

Characteristic

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted.)

OFF CHARACTERISTICS							
Collector–Emitter Breakdown Voltage	ge(3)	V _{(BR)CEO}			Vdc		
$(I_C = 1.0 \text{ mAdc}, I_B = 0)$	LMBTA05		60	_			
	LMBTA06		80	_			
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	4.0	_	Vdc	·	
$(I_E = 100 \mu Adc, I_C = 0)$							
Collector Cutoff Current		I _{CES}	_	0.1	μAdc		
$(V_{CE} = 60Vdc, I_{B} = 0)$							
Emitter Cutoff Current		I _{CBO}			μAdc		
$(V_{CB} = 60Vdc, I_{E} = 0)$	LMBTA05		_	0.1			
$(V_{CB} = 80Vdc, I_{E} = 0)$	LMBTA06			0.1			

Symbol

Min

Max

Unit

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062 \text{ in.}$
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Rev: 01.06.2018 1/3 www.leiditech.com

LMBTA05LT1G

ELECTRICAL CHARACTERISTICS (T _A = 25°C unless otherwise noted) (Continued)

ſ	Characteristic	Symbol	Min	Max	Unit	
OĪ	N CHARACTERISTICS					
ſ	DC Current Gain	h _{FE}				
	$(I_C = 10 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$		100	_		
	$(I_C = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$		100			
Ī	Collector–Emitter Saturation Voltage	$V_{CE(sat)}$			Vdc	
	$(I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc})$		_	0.25		
Ī	Base–Emitter On Voltage	V _{BE(sat)}			Vdc	
	$(I_C = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$		_	1.2		

SMALL-SIGNAL CHARACTERISTICS

Current –Gain – Bandwidth Product(4)	f	100		MHz
$(V_{CE} = 2.0 \text{ V}, I_{C} = 10\text{mA}, f = 100 \text{ MHz})$	ΙŢ	100	_	IVITIZ

^{4.} $f_{\,\scriptscriptstyle T}$ is defined as the frequency at which |h f $_{\rm e}$ | extrapolates to unity.

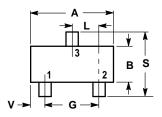
ORDERING INFORMATION

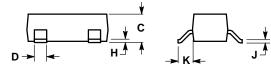
Device	Marking	Shipping
(S-)LMBTA05LT1G	1H	3000/Tape & Reel
(S-)LMBTA06LT1G	1GM	3000/Tape & Reel
(S-)LMBTA05LT3G	1H	10000/Tape & Reel
(S-)LMBTA06LT3G	1GM	10000/Tape & Reel

Rev: 01.06.2018 2/3 www.leiditech.com



SOT-23





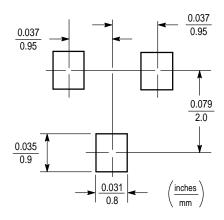
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIN	METERS
D 1111	MIN	MAX	MIN	MAX
Α	0.1102	0.1197	2.80	3.04
В	0.0472	0.0551	1.20	1.40
С	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
Н	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

PIN 1. BASE 2. EMITTER

3. COLLECTOR



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Rev: 01.06.2018 3/3 www.leiditech.com